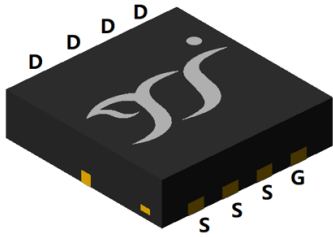
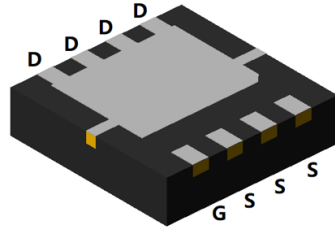


N-Channel Enhancement Mode Field Effect Transistor

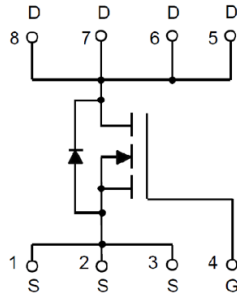


Top View



Bottom View

DFN3333-8L



Product Summary

- V_{DS} 30V
- I_D 50A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) <6.0 mohm
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) <7.0 mohm
- 100% EAS Tested

General Description

- Trench Power LV MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Moisture Sensitivity Level 3
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- High current load applications
- Load switching
- Hard switched and high frequency circuits
- Uninterruptible power supply

■ Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-source Voltage	V_{DS}	30	V	
Gate-source Voltage	V_{GS}	± 20	V	
Drain Current	I_D	$T_A=25^\circ\text{C}$	12	A
		$T_A=100^\circ\text{C}$	7	
		$T_C=25^\circ\text{C}$	50	
		$T_C=100^\circ\text{C}$	31	
Pulsed Drain Current ^A	I_{DM}	190	A	
Total Power Dissipation	P_D	$T_A=25^\circ\text{C}$	2	W
		$T_A=100^\circ\text{C}$	0.8	
		$T_C=25^\circ\text{C}$	35	
		$T_C=100^\circ\text{C}$	14	
Single Pulse Avalanche Energy ^B	E_{AS}	128	mJ	
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	3.6	$^\circ\text{C}/\text{W}$	
Thermal Resistance Junction-to- Ambient ^C	$R_{\theta JA}$	60		
Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^\circ\text{C}$	

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJQ50N03A	F1	Q50N03	5000	10000	100000	13" reel



YJQ50N03A

■ Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =250μA	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V			1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =250μA	1.0	1.5	2.5	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = 10V, I _D =15A		4.9	6.0	mΩ
		V _{GS} = 4.5V, I _D =15A		5.9	7.0	
Diode Forward Voltage	V _{SD}	I _S =20A, V _{GS} =0V			1.2	V
Maximum Body-Diode Continuous Current	I _S				50	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, f=1MHZ		2504		pF
Output Capacitance	C _{oss}			323		
Reverse Transfer Capacitance	C _{rss}			283		
Gate resistance	R _g	F= 1MHZ		1.5		Ω
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =15V, I _D =20A		54		nC
Gate-Source Charge	Q _{gs}			26		
Gate-Drain Charge	Q _{gd}			8.5		
Reverse Recovery Charge	Q _{rr}	I _F =15A, di/dt=100A/us		10.2		ns
Reverse Recovery Time	t _{rr}			15		
Turn-on Delay Time	t _{D(on)}	V _{GS} =10V, V _{DD} =20V, I _D =2A R _{GEN} =3Ω		11		ns
Turn-on Rise Time	t _r			20		
Turn-off Delay Time	t _{D(off)}			41		
Turn-off fall Time	t _f			25		

A. Repetitive rating; pulse width limited by max. junction temperature.

B. T_J=25°C, V_{DD}=24V, V_G=10V, L=1mH, I_{AS}=16A

C. The value of RθJA is measured with the device mounted on 1 in2 FR-4 board with 2oz. Copper, in the still air environment with TA =25°C. The maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.



■ Typical Performance Characteristics

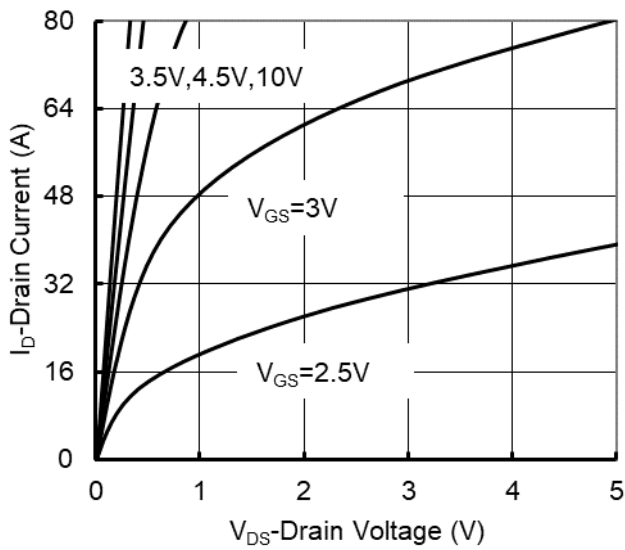


Figure1. Output Characteristics

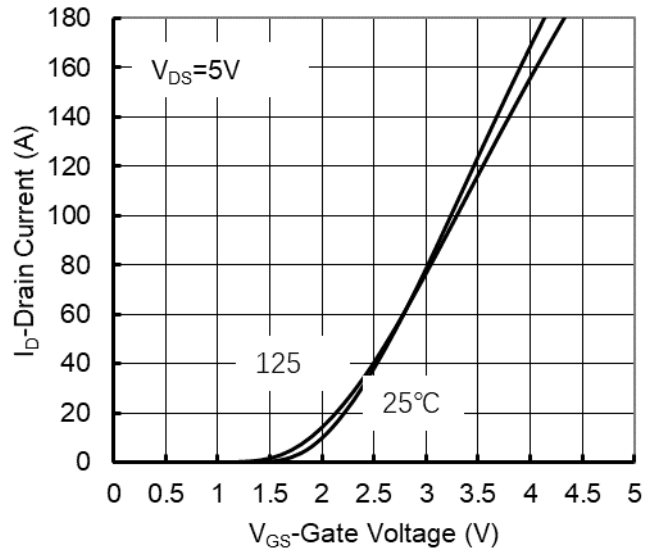


Figure2. Transfer Characteristics

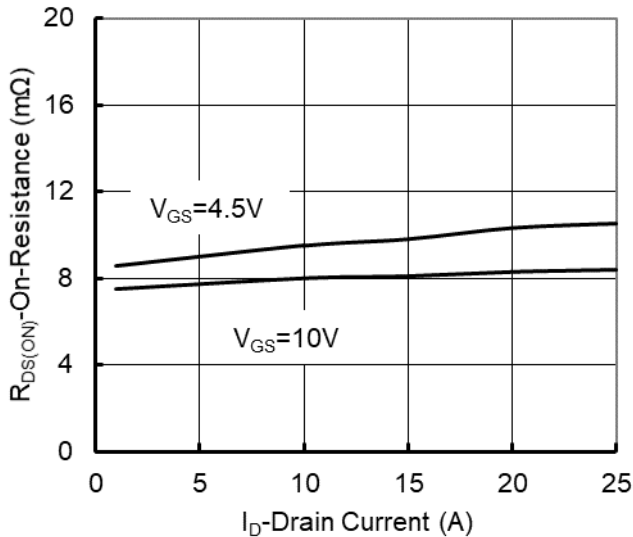


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

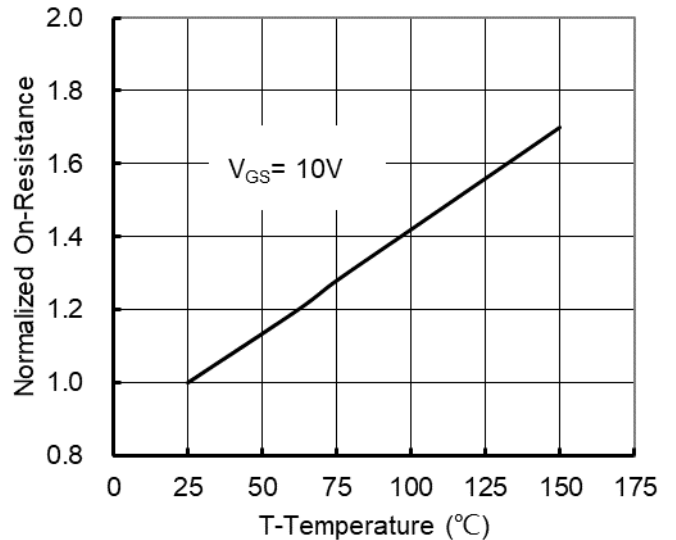


Figure 4: On-Resistance vs. Junction Temperature

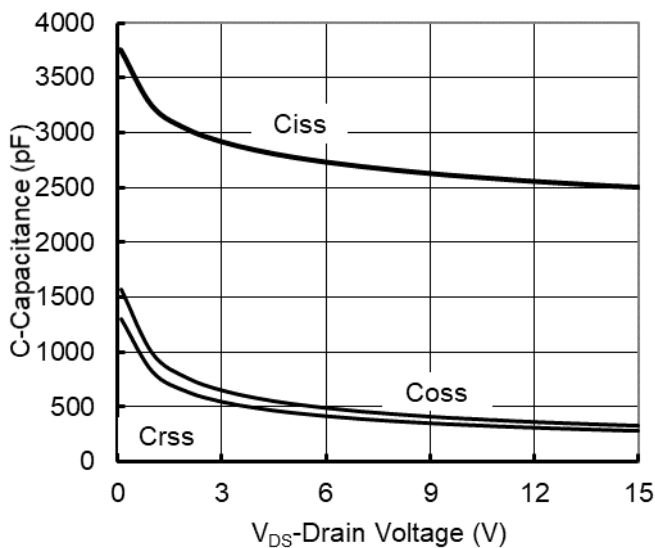


Figure5. Capacitance Characteristics

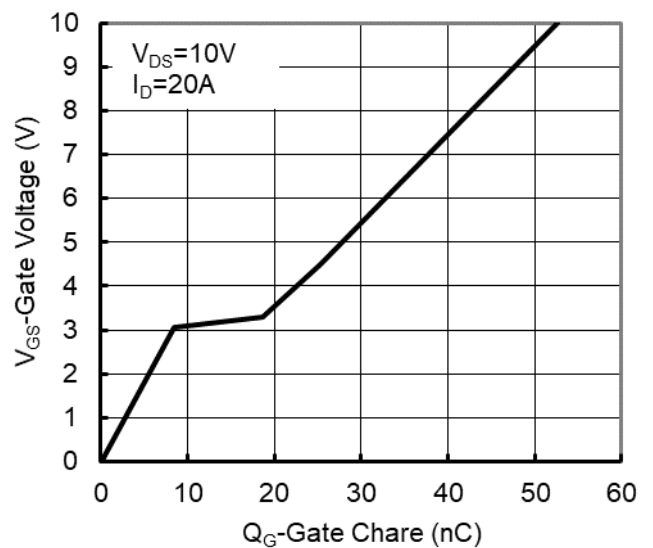


Figure6. Gate Charge



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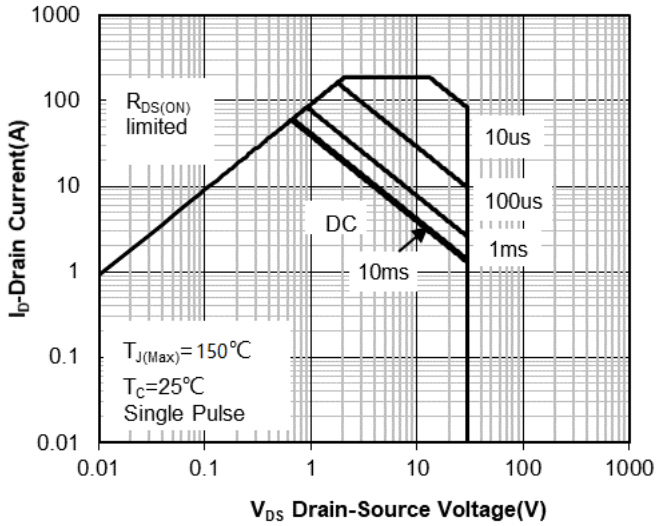


Figure7. Safe Operation Area

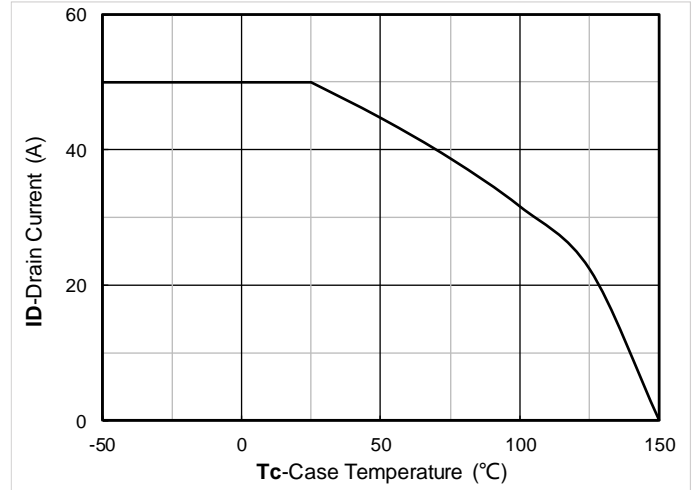


Figure8. Maximum Continuous Drain Current vs Case Temperature

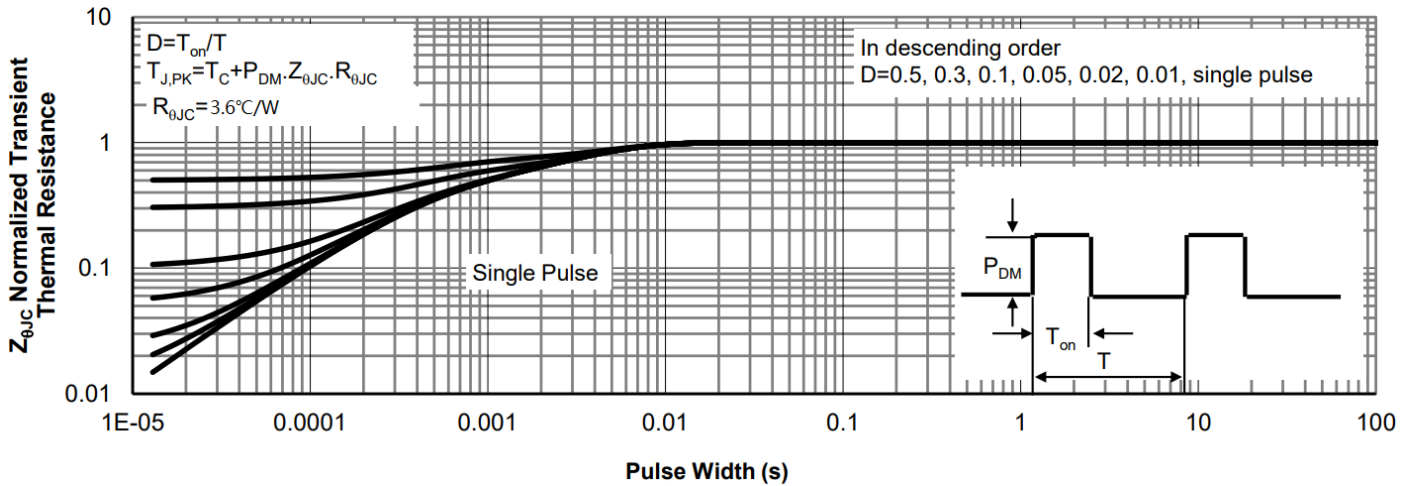
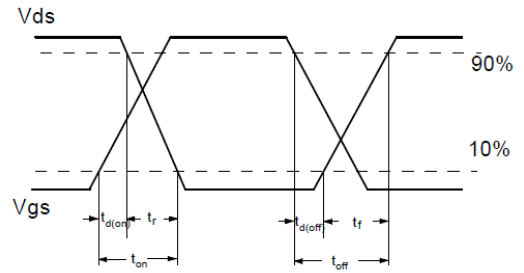
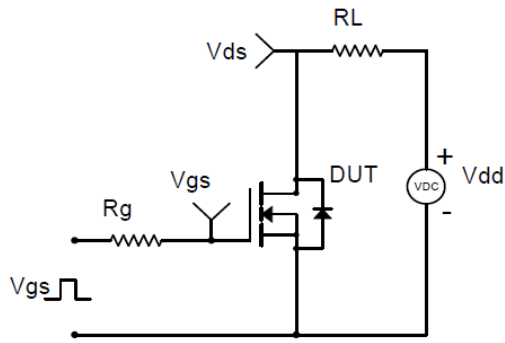
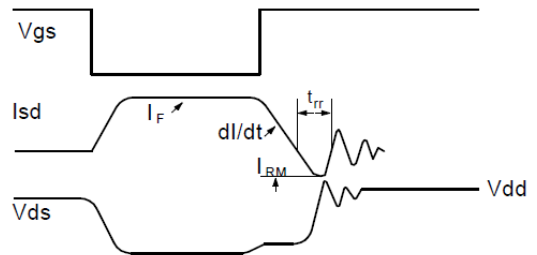
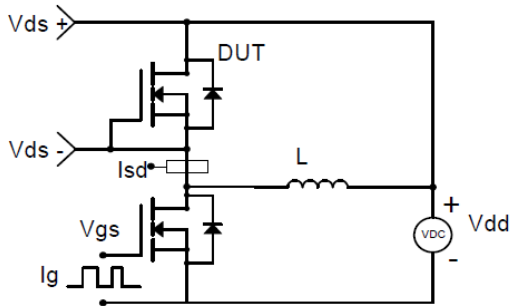


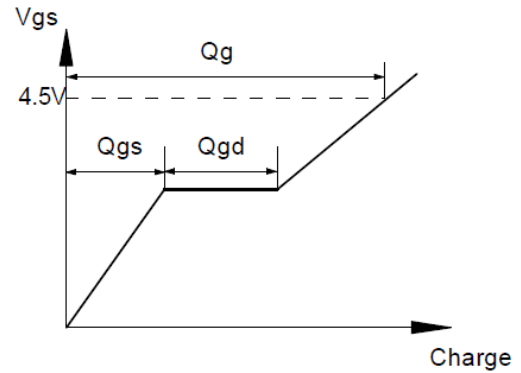
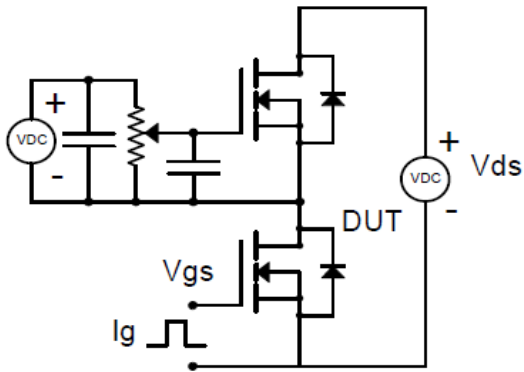
Figure9. Normalized Maximum Transient Thermal Impedance



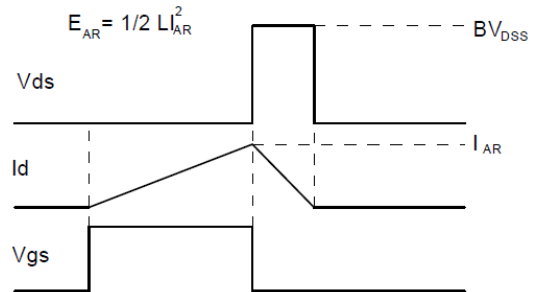
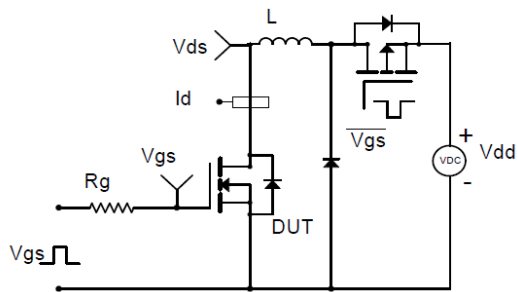
Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Gate Charge Test Circuit & Waveform

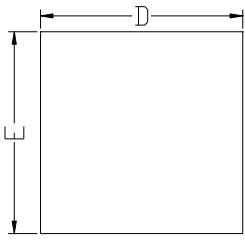


Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

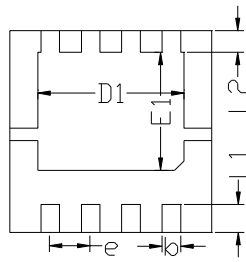


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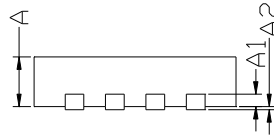
DFN3333-8L Package information



Top View
正面视图

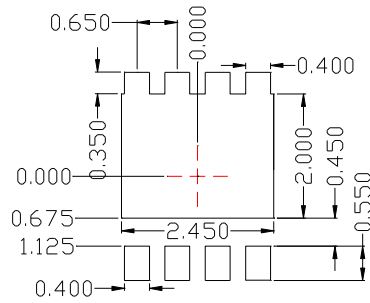


Bottom View
背面视图



Side View
侧面视图

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	3.15	3.25	3.35
E	3.15	3.25	3.35
A	0.70	0.80	0.90
A1	0.20 BSC		
A2			0.10
D1	2.20	2.35	2.50
E1	1.80	1.90	2.00
L1	0.35	0.45	0.55
L2	0.35 BSC		
b	0.20	0.30	0.40
e	0.65 BSC		



Suggested Solder Pad Layout
Top View

Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.10\text{mm}$.
3. The pad layout is for reference purposes only.



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